

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLV33F** is Designed for Operation in Band III TV Transposers and Transmitter Amplifiers from 170 to 230 MHz.

FEATURES:

- Gold Metalization
- Internal Input Matching
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	10 A
V_{CB}	60 V
V_{CE}	35 V
P_{DISS}	140 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.5 °C/W

PACKAGE STYLE .500 6L FLG

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.150/3.43	.160/4.06
B	.045/1.14	
C	.210/5.33	.220/5.59
D	.835/21.21	.865/21.97
E	.200/5.08	.210/5.33
F	.490/12.45	.510/12.95
G	.003/0.08	.007/0.18
H	.125/3.18	
I	.720/18.29	.730/18.54
J	.970/24.64	.980/24.89
K	.095/2.41	.105/2.67
L	.150/3.81	.170/4.32
M	.280/7.11	

1 = COLLECTOR 2 = BASE
3 & 4 = EMITTER

ORDER CODE: ASI10493

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 50 mA	35			V
BV_{CER}	I _C = 50 mA R _{BE} = 10 Ω	60			V
BV_{EBO}	I _E = 10 mA	4.0			V
I_{CES}	V _E = 28 V			5	mA
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	10		100	---
C_{ob}	V _{CB} = 28 V f = 1.0 MHz			80	pF
G_{PE}	V _{CE} = 25 V I _{CQ} = 3.2 A f = 225 MHz	13.5	14.5		dB
IMD₃	P _{REF} = 16 W Vision = -8 dB Side Band = -16 dB Snd. = -7 dB			-55	dBc